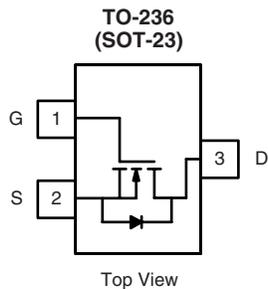


## N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (mA)
60	3 at $V_{GS} = 10$ V	240



Marking Code: 7EwI  
 E = Part Number Code for 2N7002E  
 w = Week Code  
 I = Lot Traceability

Ordering Information: 2N7002E-T1-E3 (Lead (Pb)-free)  
 2N7002E-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- Low On-Resistance: 3  $\Omega$
- Low Threshold: 2 V (typ.)
- Low Input Capacitance: 25 pF
- Fast Switching Speed: 7.5 ns
- Low Input and Output Leakage



RoHS  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### BENEFITS

- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

### APPLICATIONS

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_A = 25$ °C	240
		$T_A = 70$ °C	190
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	1300	mA
Power Dissipation	$P_D$	$T_A = 25$ °C	0.35
		$T_A = 70$ °C	0.22
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	357	°C/W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

Notes:

a. Pulse width limited by maximum junction temperature.

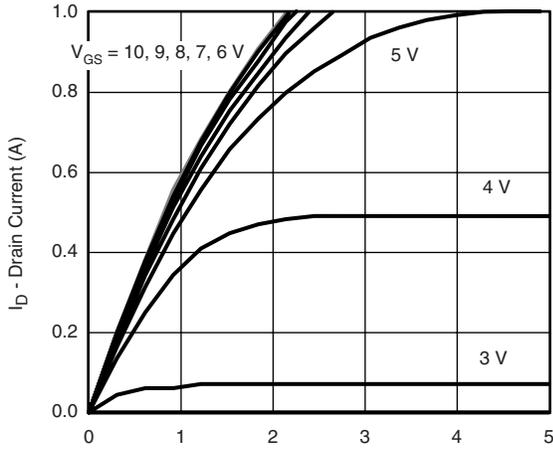
SPECIFICATIONS $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ. <sup>a</sup>	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 10\text{ }\mu\text{A}$	60	68		V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	2	2.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 15\text{ V}$			$\pm 10$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			500	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 7.5\text{ V}$	800	1300		mA
		$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}$	500	700		
Drain-Source On-Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 250\text{ mA}$		1.2	3	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 200\text{ mA}$		1.8	4	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 200\text{ mA}$		600		mS
Diode Forward Voltage	$V_{SD}$	$I_S = 200\text{ mA}, V_{GS} = 0\text{ V}$		0.85	1.2	V
<b>Dynamic<sup>a</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}$ $I_D \cong 250\text{ mA}$		0.4	0.6	nC
Gate-Source Charge	$Q_{gs}$			0.06		
Gate-Drain Charge	$Q_{gd}$			0.06		
Input Capacitance	$C_{iss}$	$V_{DS} = 5\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		21		pF
Output Capacitance	$C_{oss}$			7		
Reverse Transfer Capacitance	$C_{rss}$			2.5		
<b>Switching<sup>a, c</sup></b>						
Turn-On Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 40\text{ }\Omega$ $I_D \cong 250\text{ mA}, V_{GEN} = 10\text{ V}, R_G = 10\text{ }\Omega$		13	20	ns
Turn-Off Time	$t_{d(off)}$			18	25	

Notes:

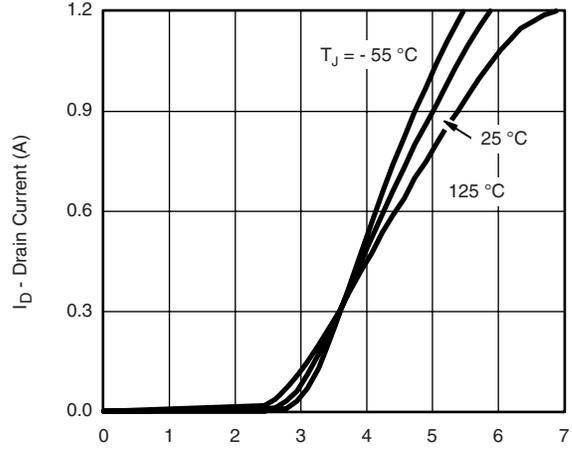
- a. For DESIGN AID ONLY, not subject to production testing.  
 b. Pulse test: pulse width  $\leq 300\text{ }\mu\text{s}$  duty cycle  $\leq 2\%$ .  
 c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

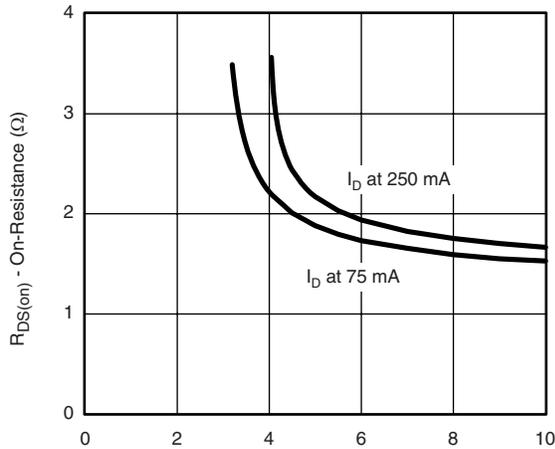
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



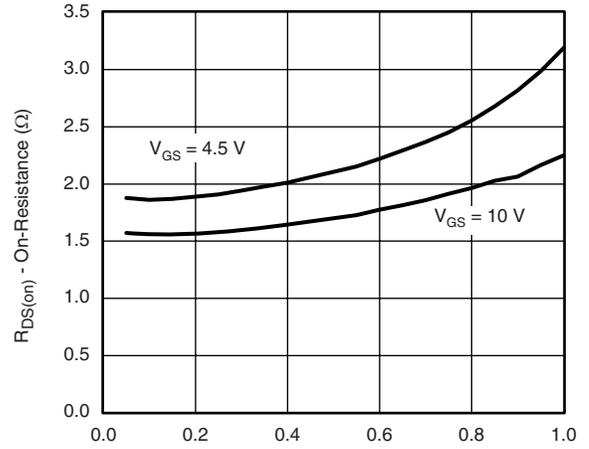
**Output Characteristics**



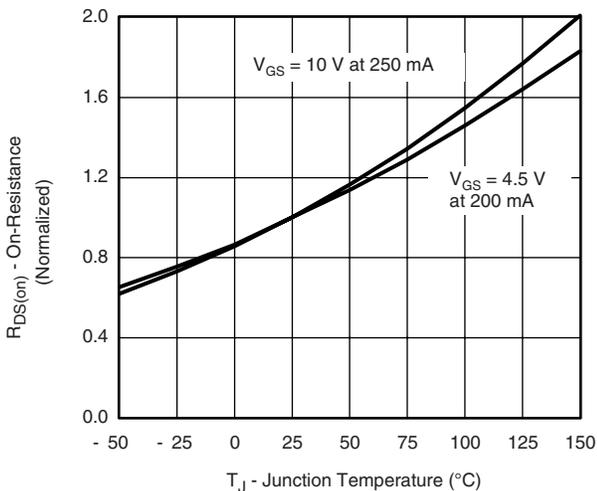
**Transfer Characteristics**



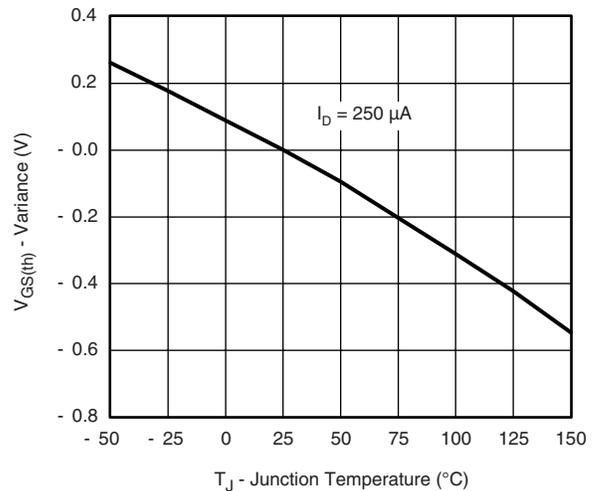
**On-Resistance vs. Gate-Source Voltage**



**On-Resistance vs. Drain Current**

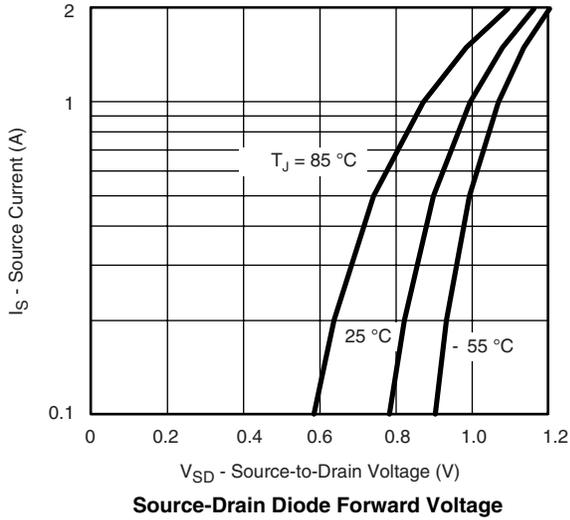
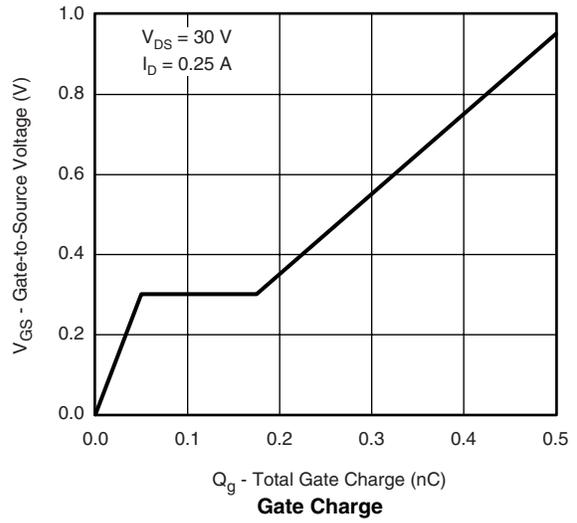
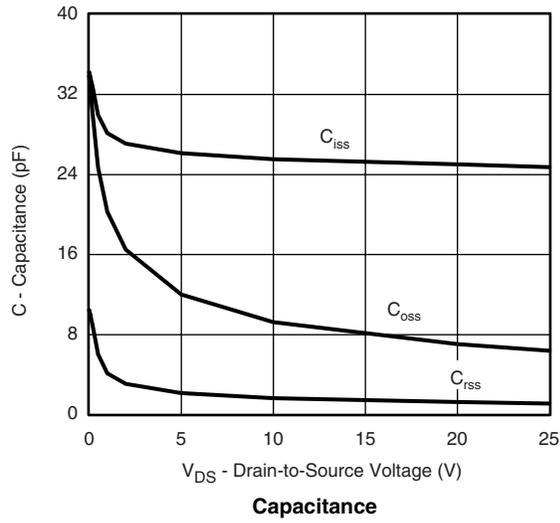


**On-Resistance vs. Junction Temperature**



**Threshold Voltage Variance Over Temperature**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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